## Thesis Title

A Thesis Submitted for the Partial Fulfillment of the Requirements for the degree of Master of Technology
in

# Dept. Name (Specialization: Specialization) 

by<br>John / Jane Doe<br>Enrollment no.: 20XXYYYXXX

Under the guidance of
Supervisor Name


DEPARTMENT OF DEPT. NAME
INDIAN INSTITUTE OF ENGINEERING SCIENCE AND
TECHNOLOGY, SHIBPUR - 711103

Department of Dept. Name
Indian Institute of Engineering
Science and Technology, Shibpur, India - 711103

## CERTIFICATE

This is to certify that we have examined the thesis entitled "Thesis Title", submitted by John / Jane Doe (Roll Number: 20XXYYYXXX), a postgraduate student of Department of Dept. Name in partial fulfillment for the award of degree of Masters in Technology with specialization of Specialization. We hereby accord our approval of it as a study carried out and presented in a manner required for its acceptance in partial fulfillment for the post graduate degree for which it has been submitted. The thesis has fulfilled all the requirements as per the regulations of the institute and has reached the standard needed for submission.

Head of Department
Prof. Susanta Kumar Parui,
Dept. of E.T.C.,
IIEST, Shibpur.

Supervisor
Supervisor Name, Dept. of E.T.C., IIEST, Shibpur.

## Examiners:

1. 
2. ...........................
3. ..........................

Place: Shibpur
Date:. .........


Department of Dept. Name
Indian Institute of Engineering
Science and Technology, Shibpur, India - 711103

## CERTIFICATE OF APPROVAL

The forgoing thesis report is hereby approved as a creditable study of "Thesis Title "carried out and presented satisfactorily to warrant its acceptance as a pre-requisite for the Degree of Master of Technology of University. It is understood that by this approval the undersigned do not necessarily approve any statement made, opinion expressed and conclusion drawn there in but approve the progress report only for the purpose for which it is submitted.

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1. ...........................
2. ...........................

Place: Shibpur
3.

Date:..........

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## ABSTRACT

In recent microprocessors or ASIC chips, the operating frequency is set by the target market.This leads to very tight timing and power constraints for the proposed circuit design. The industrial shift for adopting lower technology nodes also presents a new challenging frontier as transistors get less efficient as they undergo scaling. Analog designers are expected to optimize these conventional designs and yet meet the reduced power constraints and performance metrics imposed by various applications.

Keywords: Level shifter, energy efficient design, ultra low voltage, ULPLS, 22 nm technology.

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## Chapter 1

## Introduction

The environmental impact of global warming has accelerated the interest to adopt non-conventional power generation [1]. There are several promising sustainable energy alternatives, among which the adoption of Thermoelectric (TE) materials to scavenge the by-product heat generation is widely accepted [1]. It is crucial for applications associated with energy harvesting to posses a high figure of merit ZT $(\geq 1)[1$.

The ZT can be related to other thermoelectric parameters by ZT $=\left(\frac{\sigma_{e} \times S_{B}^{2} \times T}{\kappa_{p h}+\kappa_{e}}\right)$, where $\sigma, S_{B}, \kappa_{p h}+\kappa_{e}$, and T are the electrical conductivity, Seebeck coefficient, total thermal conductivity, and temperature value respectively [1].

Experimental and theoretical identification of two dimensional (2D) [1] or three dimensional (3D) efficient TE materials is laborious and time inefficient [1]. It is also a colossal task to compile databases of thermoelectric parameters for various synthesized TE materials and their variations with doping (n-type or p-type) [1]. Computational methods using density functional theory (DFT) are also time consuming and demand high computational complexity for exploring TE materials [1].

Efficient TE materials require a large ZT which in turn requires to maximize the Seebeck coefficient absolute value, minimize the thermal conductivity and possess a high electrical conductivity. Optimizing these parameters is a complicated task as they are inherently dependent and conflicting in nature [1]. Thus, optimizing ZT requires a thorough understanding of these various transport properties and their interrelated material characteristics.

The Seebeck coefficient depends on this energy-dependent conductivity around a fermi window centered about the fermi energy level, which is given by the Mott expression (Eq. 1.1) [1].

$$
\begin{equation*}
S_{B}=\frac{\pi^{2}}{3}\left(\frac{K_{B}^{2} \times T}{q}\right)\left[\frac{d[\ln (\sigma(E))]}{d E}\right]_{E=E_{F}}=\left(\frac{8 \pi^{2} K_{B}^{2} T}{3 q h^{2}}\right) m_{d}^{*}\left(\frac{\pi}{3 n}\right)^{2 / 3} \tag{1.1}
\end{equation*}
$$

where n is the carrier concentration and effective mass $m_{d}^{*}$ of the carrier when present in the conduction band or valence band. This effective mass $\left(m_{d}^{*}\right)$ is obtained from the function of the density of states (DOS) and is thus also known as $m_{D O S}^{*}$ [1]. The underlying assumption for the final closed form expression is the presence of a parabolic band and an energy-independent scattering approximation [1]. The electrical conductivity $\left(\sigma_{e}\right)$ can be approximated by the Drude model in terms of its carrier concentration (n) and mobility $(\mu)$ as shown in Eqn. 1.3. Thus, the influence of carrier concentration impacts both the parameters contradictorily as shown in Fig. 1.1.


Figure 1.1: Figure 1.1

$$
\begin{equation*}
\sigma_{e}=n q \mu=\frac{n q^{2} \tau}{m} \tag{1.2}
\end{equation*}
$$

$$
\begin{gather*}
\kappa=\kappa_{p h}+\kappa_{e}=\left(\frac{\pi^{2}}{3}\right)\left(\frac{n K_{B}^{2} T \tau}{m}\right)+L_{n} \times \sigma_{e} T  \tag{1.3}\\
L_{n} \approx\left(\frac{\pi^{2}}{3}\right)\left(\frac{K_{B}}{q}\right)^{2} \tag{1.4}
\end{gather*}
$$

### 1.1 Section 1.1

### 1.1.1 Sub-Section 1.1.1

content.

### 1.1.2 Sub-Section 1.1.1

content.

Thesis Title

| Material | Crystal | Space Group | Bandgap(ev) | $\begin{aligned} & \text { Direct } \\ & \text { / In- } \\ & \text { direct } \end{aligned}$ | $\kappa\left(W m^{-1} k^{-1}\right)$ | $\sigma_{e}\left(\times 10^{-3} \mathrm{Scm}^{-1} 1\right)$ | ZT(10-4) |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| xxx | xxx | xxxxx | YYYXXXX ZZZ exp. YYYexp XXXexp, | Direct | ZZ exp, | YY exp, | XX exp, |

## Chapter 2

## Methodology

Table 2.1: Table Caption

| Database | Crystal in- <br> formation | Mechanical <br> parameters | Thermodynamic <br> parameters | Electronic <br> parameters |
| :--- | :--- | :--- | :--- | :--- |
|  |  |  |  |  |
| Database 1 | Y | Y | Y | Y |
| Database 2 | Y | Y | Y | Y |
| Database 3 | Y | Y | Y | Y |
| Database 4 | Y | Y | Y | Y |
| Database 5 | Y | N | Y | Y |

## Chapter 3

## Chapter 3

- Item1
- Item2
- Item3
- Item4
- Item5
- Item6


## Chapter 4

## Chapter 4



Figure 4.1: My caption.

## Chapter 5

## Chapter 5

5.1 Summary

- Item1
- Item2
- Item3
- Item4
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- Item6


### 5.2 Future Work

### 5.2.1 Work Breakdown Structure (WBS)

- Item1
- Item2
- Item3

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- Item4
- Item5
- Item6


## Chapter 6

## Chapter 6

## References

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## APPENDIX-A: Guide



## APPENDIX-A: Guide



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